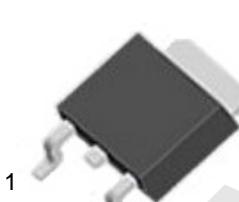
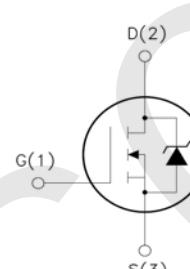


SM20N06 60V N-Channel MOSFET Features: <ul style="list-style-type: none"> <input type="checkbox"/> Low Intrinsic Capacitances. <input type="checkbox"/> Excellent Switching Characteristics. <input type="checkbox"/> Extended Safe Operating Area. <input type="checkbox"/> Unrivalled Gate Charge :$Q_g = 25.3\text{nC}$ (Typ.). <input type="checkbox"/> $\text{BV}_{\text{DSS}}=60\text{V}, I_{\text{D}}=20\text{A}$ <input type="checkbox"/> $R_{\text{DS(on)}} : 0.035\Omega$ (Max) @ $V_{\text{G}}=10\text{V}$ <input type="checkbox"/> 100% Avalanche Tested 	 TO-252   1. Gate (G) 2. Drain (D) 3. Source (S)
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Absolute Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	60	V
I_{D}	Drain Current	$T_c=25^\circ\text{C}$	A
		$T_c=100^\circ\text{C}$	
$V_{\text{GS(TH)}}$	Gate Threshold Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (note1)	72	mJ
I_{AR}	Avalanche Current (note2)	20	A
P_{D}	Power Dissipation ($T_a=25^\circ\text{C}$)	40	W
T_j	Junction Temperature(Max)	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	
T_L	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\text{θJC}}$	Thermal Resistance,Junction to Case	-	3.2	$^\circ\text{C/W}$

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=60\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$\text{V}_{\text{GS}}=\pm20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$\text{V}_{\text{GS}(\text{th})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	1.2	1.6	2.5	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=20\text{A}$	-	24	35	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_D=20\text{A}$		30	40	
Forward Transconductance	g_{FS}	$\text{V}_{\text{DS}}=5\text{V}, \text{I}_D=5\text{A}$	11	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=15\text{V}, \text{V}_{\text{GS}}=0\text{V},$ $F=1.0\text{MHz}$	-	590	-	PF
Output Capacitance	C_{oss}		-	70	-	PF
Reverse Transfer Capacitance	C_{rss}		-	64	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$\text{V}_{\text{DD}}=30\text{V}, \text{I}_D=2\text{A},$ $\text{V}_{\text{GS}}=10\text{V}, \text{R}_G=3\Omega$	-	6	-	nS
Turn-on Rise Time	t_r		-	6.1	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	17	-	nS
Turn-Off Fall Time	t_f		-	3	-	nS
Total Gate Charge	Q_g	$\text{V}_{\text{DS}}=30\text{V}, \text{I}_D=10\text{A},$ $\text{V}_{\text{GS}}=10\text{V}$	-	25.3	-	nC
Gate-Source Charge	Q_{gs}		-	4.7	-	nC
Gate-Drain Charge	Q_{gd}		-	6.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_S=20\text{A}$	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	20	A
Reverse Recovery Time	t_{rr}	$\text{T}_J = 25^\circ\text{C}, \text{I}_F = 20\text{A}$ $d\text{i}/dt = 100\text{A}/\mu\text{s}$ (Note 3)	-	29.5	-	nS
Reverse Recovery Charge	Q_{rr}		-	50	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $\text{T}_J=25^\circ\text{C}, \text{V}_{\text{DD}}=30\text{V}, \text{V}_{\text{G}}=10\text{V}, \text{L}=0.5\text{mH}, \text{R}_G=25\Omega$

Typical Characteristics

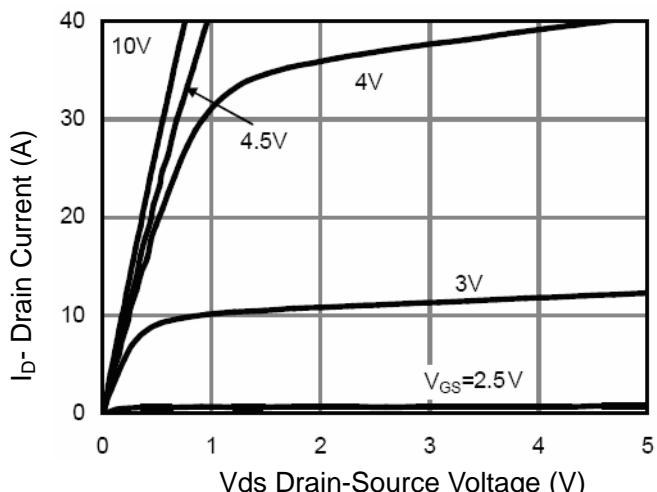


Figure 1 Output Characteristics

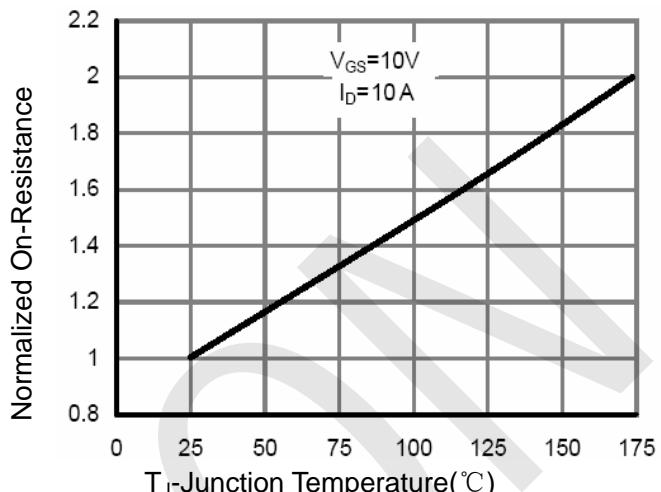


Figure 4 Rdson-Junction Temperature

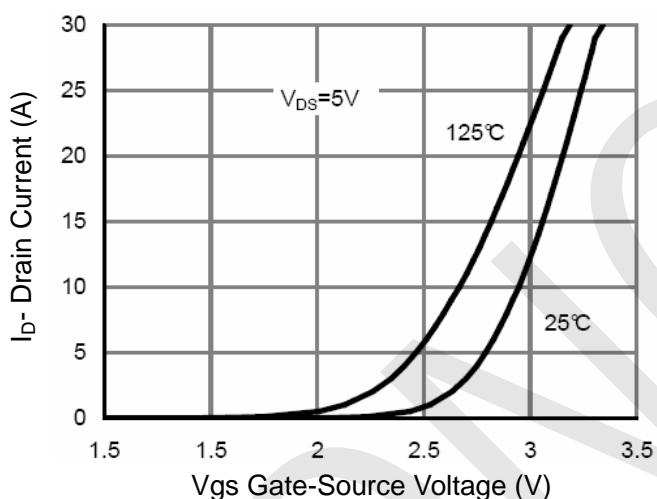


Figure 2 Transfer Characteristics

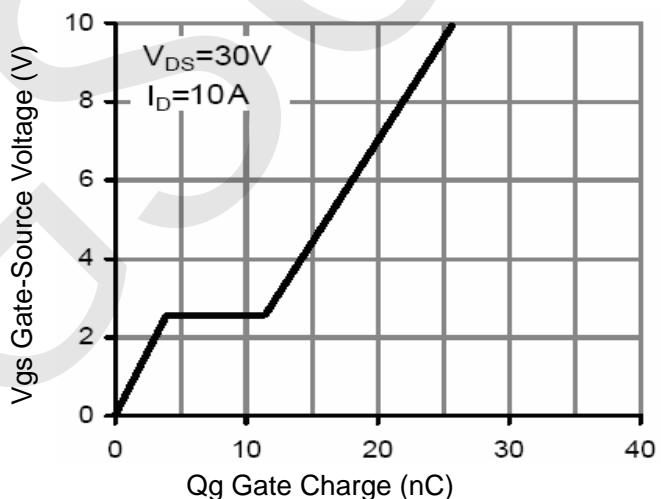


Figure 5 Gate Charge

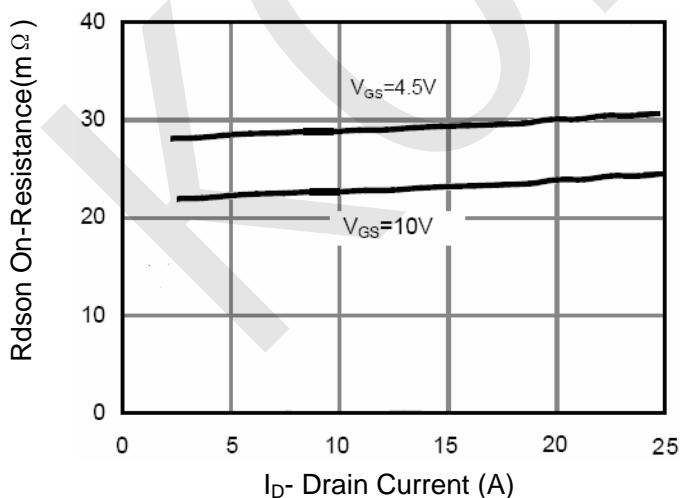


Figure 3 Rdson- Drain Current

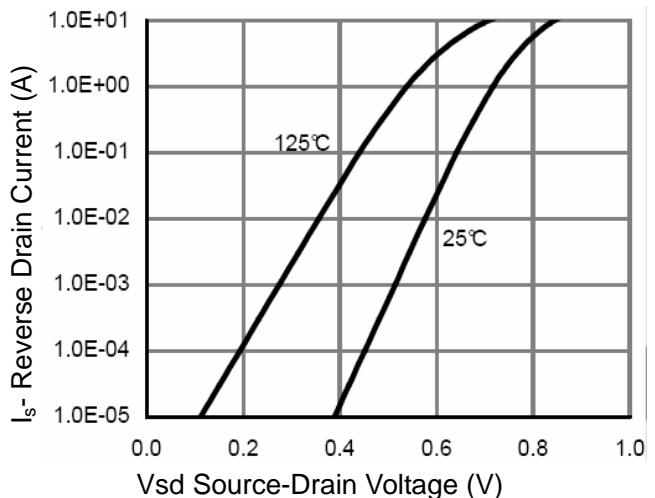


Figure 6 Source- Drain Diode Forward

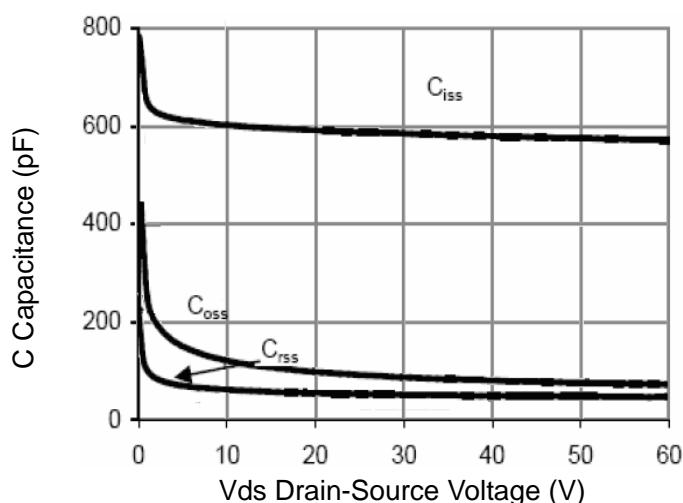


Figure 7 Capacitance vs Vds

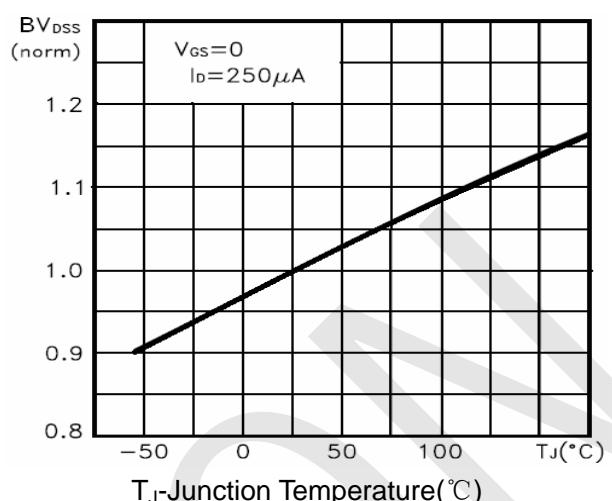


Figure 9 BV_{DSS} vs Junction Temperature

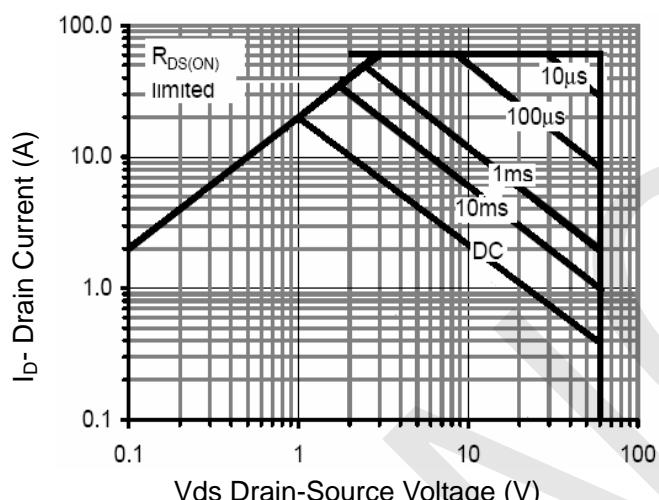


Figure 8 Safe Operation Area

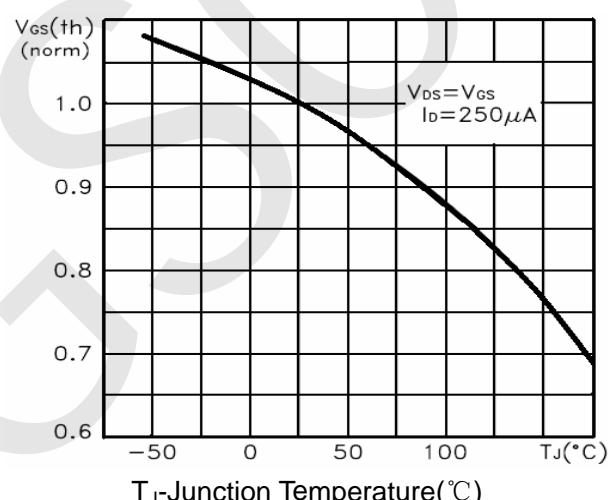


Figure 10 $V_{GS(\text{th})}$ vs Junction Temperature

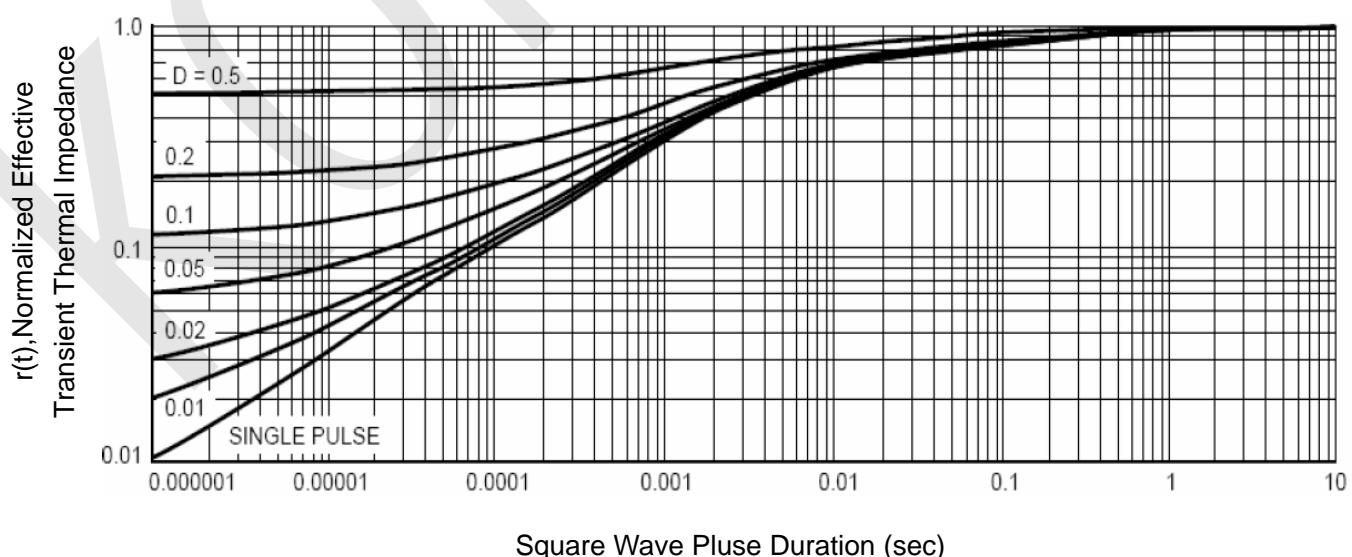
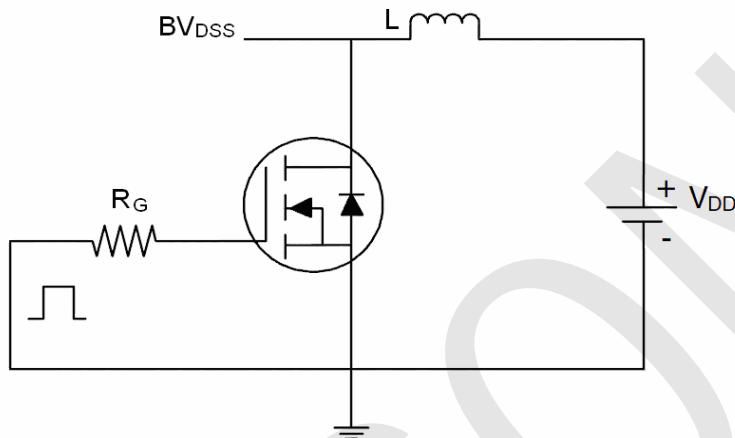


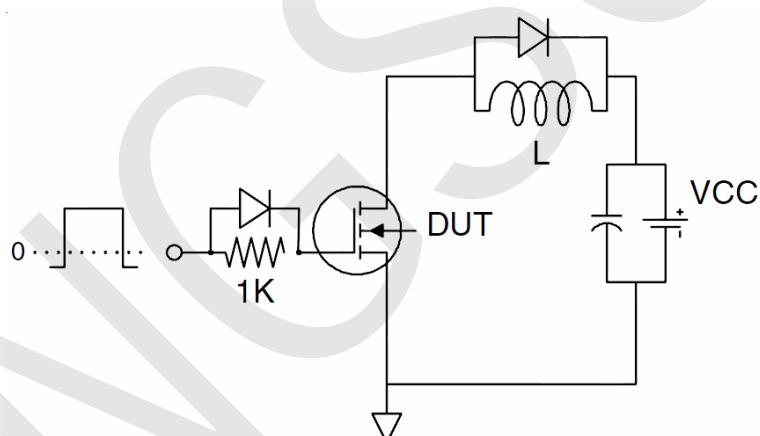
Figure 11 Normalized Maximum Transient Thermal Impedance

Test Circuit

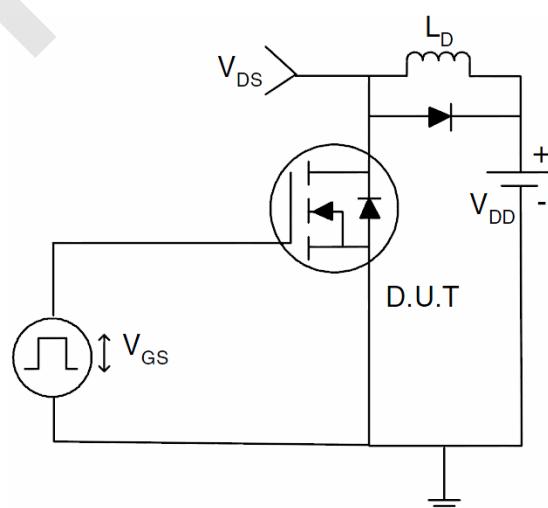
1) E_{AS} test Circuit



2) Gate charge test Circuit



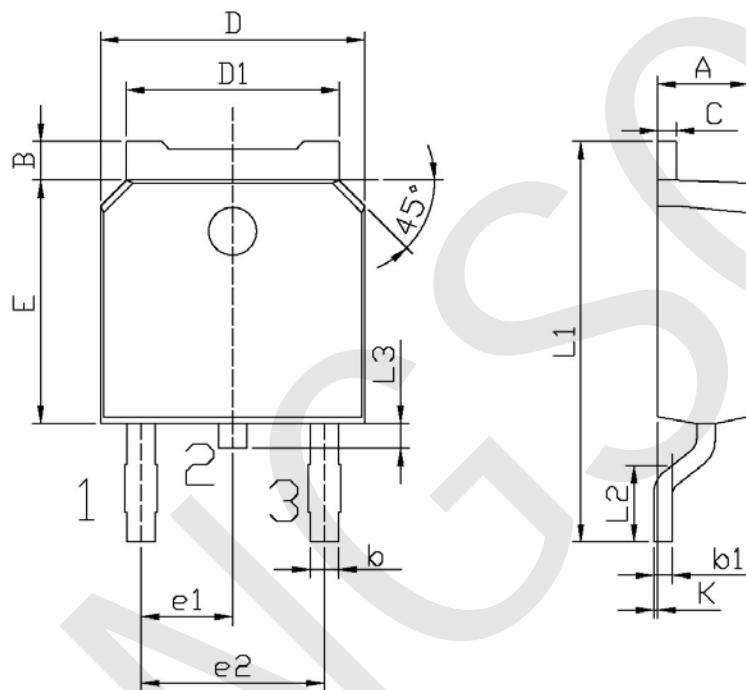
3) Switch Time Test Circuit



Package Dimension

TO-252

Unit:mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.20	5.40	K	0.00	0.10